

Abstract**Single crystal of silicon with $\langle 100 \rangle$ orientation, which is doped with n-type dopant, and method for producing such a single crystal**

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Single crystal of silicon with $\langle 100 \rangle$ orientation and method for producing a single crystal from silicon with $\langle 100 \rangle$ orientation. The single crystal is doped with n-type dopant and comprises a starting cone, a cylindrical portion and an end cone, a crystal angle in a middle portion of the starting cone, the length of which is not less than 50% of a length of the starting cone, being not less than 20° and not greater than 30° , and edge facets extending from a periphery of the single crystal into the single crystal, the edge facets in the starting cone and in the cylindrical portion of the single crystal in each case having a length which is not more than $700\ \mu\text{m}$.

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Drawing for the abstract: Fig.5